

PBSS4032SP

30 V, 4.8 A PNP/PNP low V_{CEsat} (BISS) transistor Rev. 2 — 13 October 2010 Pro

Product data sheet

Product profile 1.

1.1 General description

PNP/PNP low V_{CEsat} Breakthrough In Small Signal (BISS) transistor in a SOT96-1 (SO8) medium power Surface-Mounted Device (SMD) plastic package.

Table 1. **Product overview**

Type number	Package N		NPN/NPN	NPN/PNP
	Nexperia	Name	complement	complement
PBSS4032SP	SOT96-1	SO8	PBSS4032SN	PBSS4032SPN

1.2 Features and benefits

- Low collector-emitter saturation voltage V_{CEsat}
- Optimized switching time
- High collector current capability I_C and I_{CM}
- High collector current gain (h_{FE}) at high I_C
- High efficiency due to less heat generation
- Smaller required Printed-Circuit Board (PCB) area than for conventional transistors

1.3 Applications

- DC-to-DC conversion
- Battery-driven devices
- Power management
- Charging circuits

1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	-30	V
I _C	collector current		-	-	-4.8	Α
I _{CM}	peak collector current	single pulse; $t_p \le 1 \text{ ms}$	-	-	-10	Α
R _{CEsat}	collector-emitter saturation resistance	$I_C = -4 \text{ A}; I_B = -0.4 \text{ A}$	l -	65	98	mΩ

^[1] Pulse test: $t_p \le 300 \ \mu s$; $\delta \le 0.02$.



2. Pinning information

Table 3. Pinning

	9		
Pin	Description	Simplified outline	Graphic symbol
1	emitter TR1		
2	base TR1	8月月月5	8 7 6 5
3	emitter TR2		TR1 L TR2 L
4	base TR2		
5	collector TR2	1 1 1 1 4	1 2 3 4
6	collector TR2		006aaa976
7	collector TR1		
8	collector TR1		

3. Ordering information

Table 4. Ordering information

Type number	Package	Package		
	Name	Description	Version	
PBSS4032SP	SO8	plastic small outline package; 8 leads; body width 3.9 mm	SOT96-1	

4. Marking

Table 5. Marking codes

Type number	Marking code
PBSS4032SP	4032SP

5. Limiting values

Table 6. Limiting values

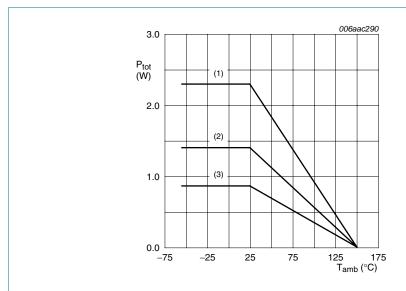
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per transis	stor				
V_{CBO}	collector-base voltage	open emitter	-	-30	V
V_{CEO}	collector-emitter voltage	open base	-	-30	V
V_{EBO}	emitter-base voltage	open collector	-	- 5	V
I _C	collector current		-	-4.8	Α
I _{CM}	peak collector current	$single \ pulse; \\ t_p \leq 1 \ ms$	-	-10	Α
I_{B}	base current		-	-1	Α
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$	<u>[1]</u> _	0.73	W
			[2] _	1	W
			[3]	1.7	W

Table 6. Limiting values ...continued In accordance with the Absolute Maximum Rating System (IEC 60134).

		<i>y</i> , ,	,		
Symbol	Parameter	Conditions	Min	Max	Unit
Per device					
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$	[1] -	0.86	W
			[2] _	1.4	W
			[3] _	2.3	W
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		–55	+150	°C
T _{stg}	storage temperature		–65	+150	°C
-					

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².
- [3] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.



- (1) Ceramic PCB, Al_2O_3 , standard footprint
- (2) FR4 PCB, mounting pad for collector 1 cm²
- (3) FR4 PCB, standard footprint

Fig 1. Per device: Power derating curves

6. Thermal characteristics

Table 7. Thermal characteristics

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per trans	sistor					
$R_{\text{th(j-a)}}$ thermal resistance from in free air junction to ambient	thermal resistance from	in free air	<u>[1]</u> _	-	170	K/W
	[2] _	-	125	K/W		
			[3] _	-	75	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point		-	-	40	K/W
Per devi	ce					
R _{th(j-a)}	thermal resistance from	in free air	<u>[1]</u> -	-	145	K/W
	junction to ambient		[2] _	-	90	K/W
			[3] _	-	55	K/W
-						

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².
- [3] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.

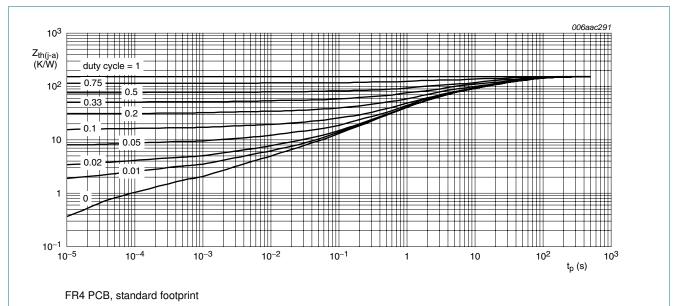
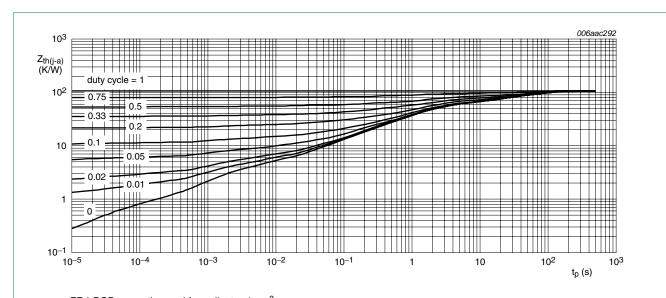
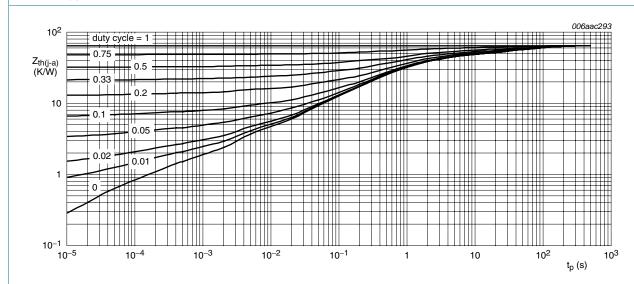


Fig 2. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for collector 1 cm²

Fig 3. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



Ceramic PCB, Al₂O₃, standard footprint

Fig 4. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

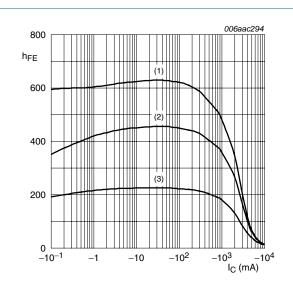
7. Characteristics

Table 8. Characteristics

 T_{amb} = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per tran	sistor						
I _{CBO}	collector-base	$V_{CB} = -30 \text{ V}; I_E = 0 \text{ A}$		-	-	-100	nA
	cut-off current	$V_{CB} = -30 \text{ V}; I_E = 0 \text{ A};$ $T_j = 150 \text{ °C}$		-	-	-50	μА
I _{CES}	collector-emitter cut-off current	$V_{CE} = -24 \text{ V}; V_{BE} = 0 \text{ V}$		-	-	-100	nA
I _{EBO}	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_C = 0 \text{ A}$		-	-	-100	nA
h _{FE}	DC current gain	$V_{CE} = -2 V$	[1]				
		$I_C = -500 \text{ mA}$		200	380	-	
		$I_C = -1 A$		200	330	-	
		I _C = −2 A		150	250	-	
		$I_C = -4 A$		60	100	-	
		$I_C = -5 A$		40	60	-	
V_{CEsat}	collector-emitter		[1]				
	saturation voltage	$I_C = -1 A$; $I_B = -50 \text{ mA}$		-	-115	-165	mV
	$I_C = -1 A$; $I_B = -10 \text{ mA}$		-	-170	-240	mV	
	$I_C = -2 \text{ A}; I_B = -40 \text{ mA}$		-	-210	-300	mV	
		$I_C = -4 \text{ A}; I_B = -400 \text{ mA}$		-	-260	-390	mV
		$I_C = -4 \text{ A}; I_B = -200 \text{ mA}$		-	-300	-450	mV
		$I_C = -5 \text{ A}; I_B = -250 \text{ mA}$		-	-340	-510	mV
R _{CEsat}	collector-emitter saturation resistance	$I_C = -4 A$; $I_B = -400 \text{ mA}$	[1]	-	65	98	mΩ
V_{BEsat}	base-emitter		[1]				
	saturation voltage	$I_C = -1 A$; $I_B = -100 \text{ mA}$		-	-0.8	-0.9	V
		$I_C = -4 \text{ A}; I_B = -400 \text{ mA}$		-	-0.99	-1.1	V
V_{BEon}	base-emitter turn-on voltage	$V_{CE} = -2 \text{ V}; I_{C} = -2 \text{ A}$	[1]	-	-0.81	-0.9	V
t _d	delay time	$V_{CC} = -12.5 \text{ V}; I_C = -1 \text{ A};$		-	30	-	ns
t _r	rise time	$I_{Bon} = -0.05 \text{ A}; I_{Boff} = 0.05 \text{ A}$		-	60	-	ns
t _{on}	turn-on time			-	90	-	ns
ts	storage time			-	140	-	ns
t _f	fall time			-	80	-	ns
t _{off}	turn-off time			-	220	-	ns
f _T	transition frequency	$V_{CE} = -10 \text{ V}; I_{C} = -100 \text{ mA}; f = 100 \text{ MHz}$		-	115	-	MHz
C _c	collector capacitance	$V_{CB} = -10 \text{ V}; I_E = i_e = 0 \text{ A};$ f = 1 MHz		-	85	-	pF

^[1] Pulse test: $t_p \le 300 \ \mu s; \ \delta \le 0.02.$



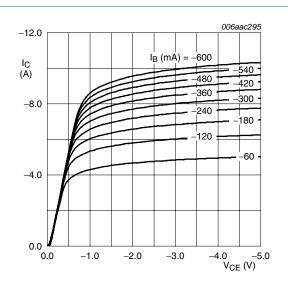
$$V_{CE} = -2 V$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

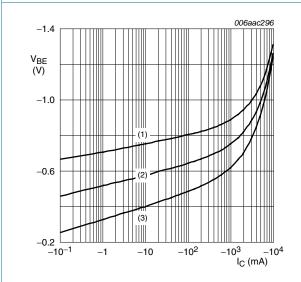
(3)
$$T_{amb} = -55 \, ^{\circ}C$$

Fig 5. DC current gain as a function of collector current; typical values



 $T_{amb} = 25 \, ^{\circ}C$

Fig 6. Collector current as a function of collector-emitter voltage; typical values



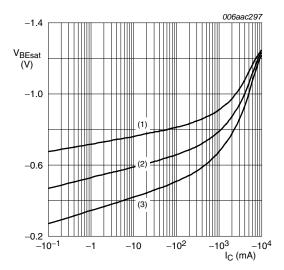
$$V_{CE} = -2 V$$

(1)
$$T_{amb} = -55 \,^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig 7. Base-emitter voltage as a function of collector current; typical values



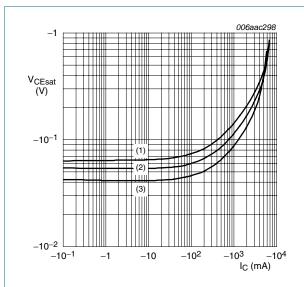
$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = -55 \,^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig 8. Base-emitter saturation voltage as a function of collector current; typical values



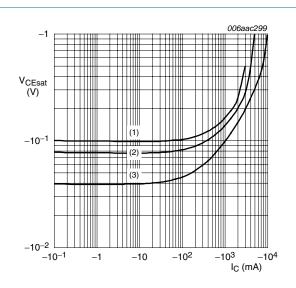
$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -55 \, ^{\circ}C$$

Fig 9. Collector-emitter saturation voltage as a function of collector current; typical values



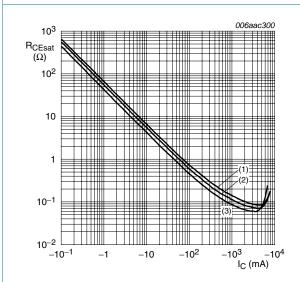
$$T_{amb} = 25 \, ^{\circ}C$$

(1)
$$I_C/I_B = 100$$

(2)
$$I_C/I_B = 50$$

(3)
$$I_C/I_B = 10$$

Fig 10. Collector-emitter saturation voltage as a function of collector current; typical values



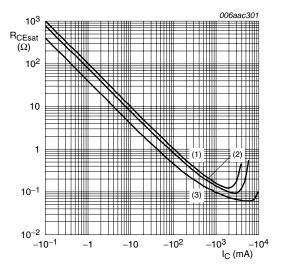


(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -55 \, ^{\circ}C$$

Fig 11. Collector-emitter saturation resistance as a function of collector current; typical values



(1)
$$I_C/I_B = 100$$

(2)
$$I_C/I_B = 50$$

(3)
$$I_C/I_B = 10$$

Fig 12. Collector-emitter saturation resistance as a function of collector current; typical values

8. Test information

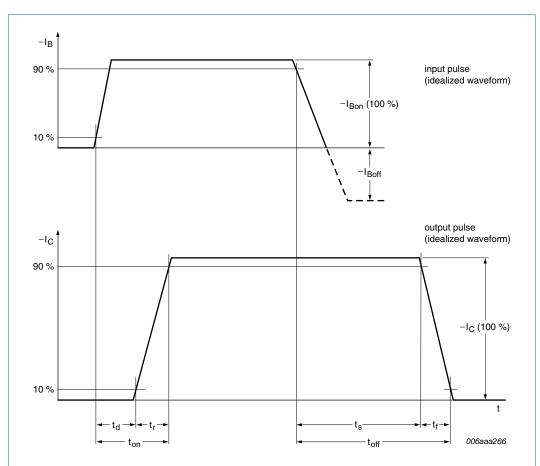
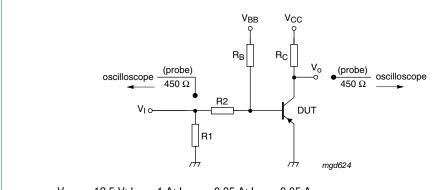


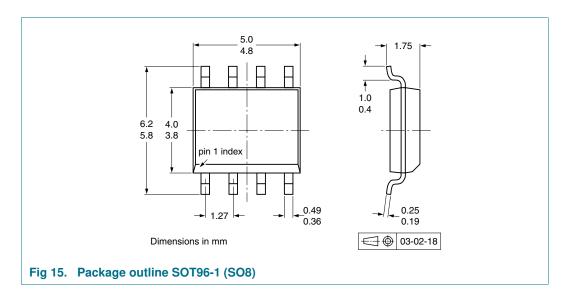
Fig 13. BISS transistor switching time definition



 $V_{CC} = -12.5 \text{ V}; I_C = -1 \text{ A}; I_{Bon} = -0.05 \text{ A}; I_{Boff} = 0.05 \text{ A}$

Fig 14. Test circuit for switching times

9. Package outline



10. Packing information

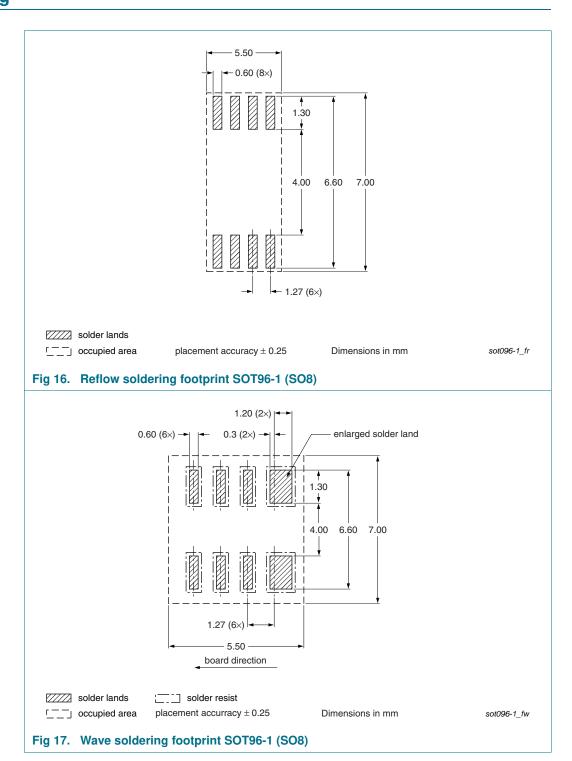
Table 9. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing	quantity
			1000	2500
PBSS4032SP	SOT96-1	8 mm pitch, 12 mm tape and reel	-115	-118

^[1] For further information and the availability of packing methods, see Section 14.

11. Soldering



PBSS4032SP

30 V, 4.8 A PNP/PNP low V_{CEsat} (BISS) transistor

12. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PBSS4032SP v.2	20101013	Product data sheet	-	PBSS4032SP v.1
Modifications:	• Figure 1 "Pe	er device: Power derating c	urves": updated.	
PBSS4032SP v.1	20100714	Product data sheet	-	-

13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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PBSS4032SP

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